

2SB0928 (2SB928), 2SB0928A (2SB928A)

Silicon PNP epitaxial planar type

For Power amplification

For TV vertical deflection output

Complementary to 2SD1250 and 2SD1250A

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- High collector power dissipation P_C
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-200	V
Collector-emitter voltage (Base open)	2SB0928	V_{CEO}	-150
	2SB0928A		-180
Emitter-base voltage (Collector open)	V_{EBO}	-6	V
Collector current	I_C	-2	A
Peak collector current	I_{CP}	-3	A
Collector power dissipation	P_C	30	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

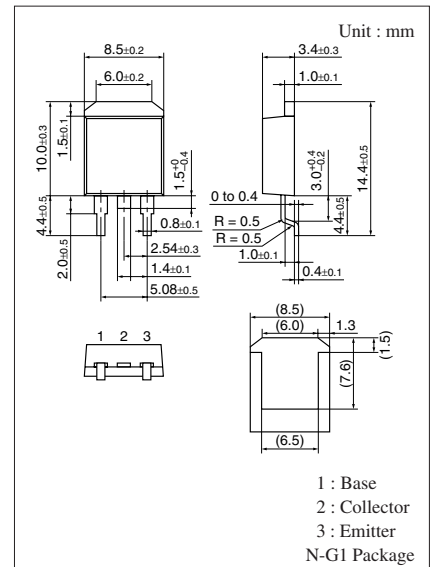
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -500 \mu\text{A}$, $I_E = 0$	-200			V
Collector-emitter voltage (Base open)	2SB0928	$I_C = -5 \text{ mA}$, $I_B = 0$	-150			V
	2SB0928A		-180			
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -500 \mu\text{A}$, $I_C = 0$	-6			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -200 \text{ V}$, $I_E = 0$			-50	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -4 \text{ V}$, $I_C = 0$			-50	μA
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -10 \text{ V}$, $I_C = -150 \text{ mA}$	60		240	—
	h_{FE2}	$V_{CE} = -10 \text{ V}$, $I_C = -400 \text{ mA}$	50			
Base-emitter voltage	V_{BE}	$V_{CE} = -10 \text{ V}$, $I_C = -400 \text{ mA}$			-1.0	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$			-1.0	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}$, $I_C = -0.5 \text{ A}$, $f = 10 \text{ MHz}$		40		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

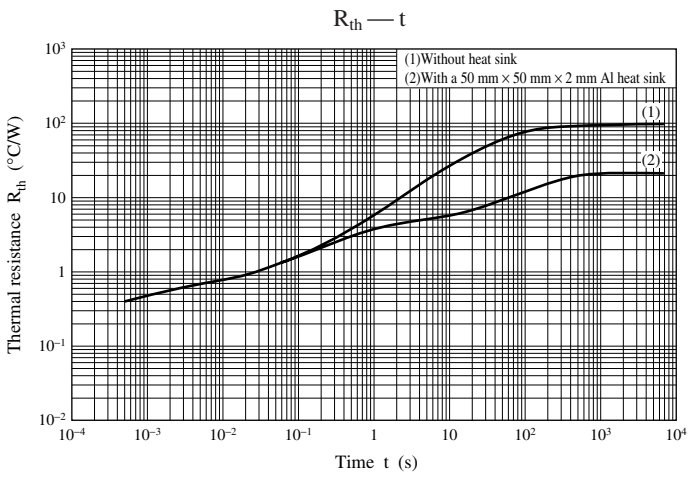
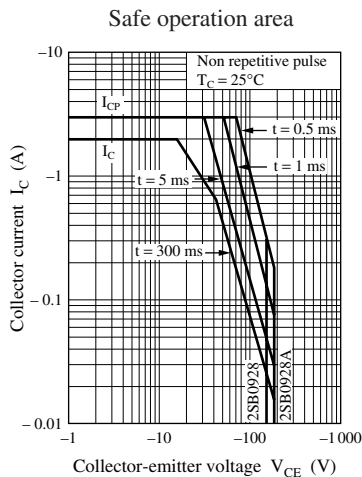
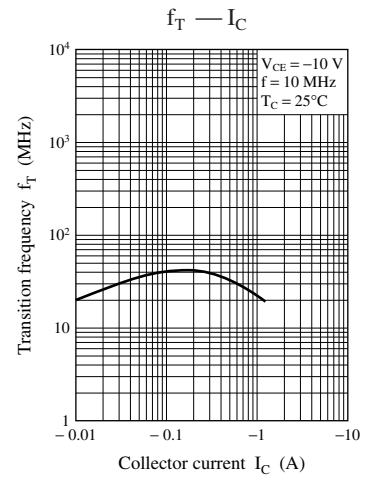
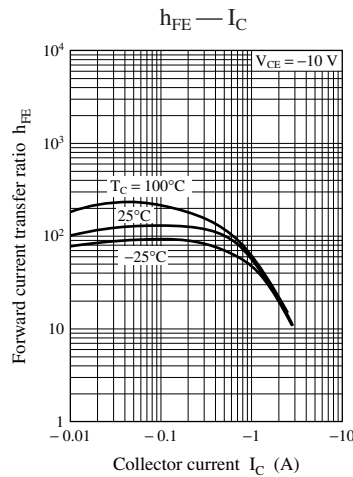
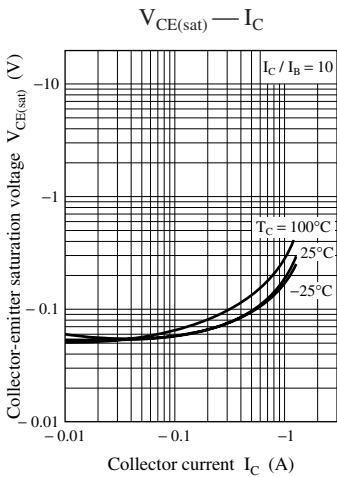
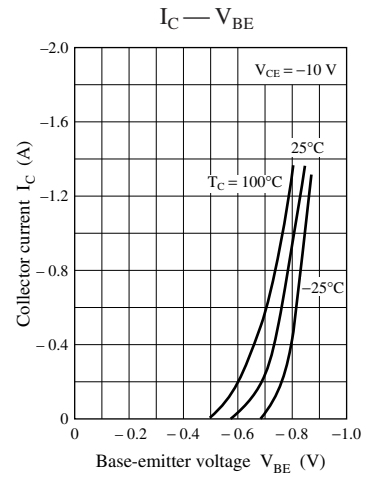
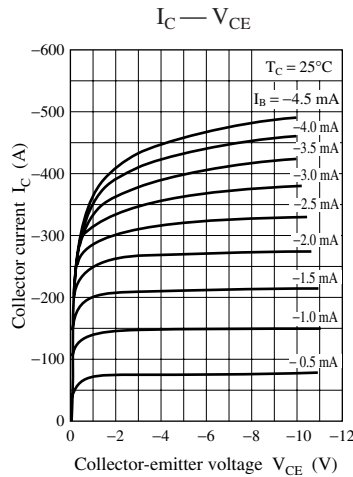
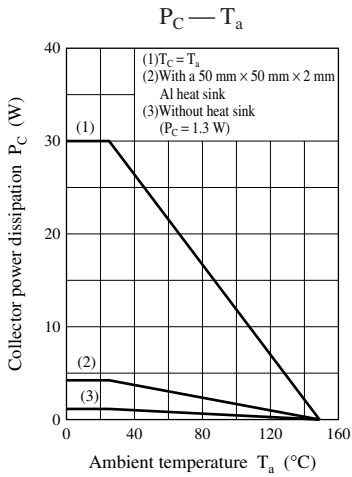
2. *: Rank classification

Rank	Q	P
h_{FE1}	60 to 140	100 to 240

Note) The part numbers in the parenthesis show conventional part number.



Note) Self-supported type package is also prepared



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